





Developments in AC-LGADs for future colliders and nuclear physics experiments

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- Silicon low-gain avalanche diodes (LGADs) are studied by the CMS and ATLAS experiments for their endcap timing detector upgrades
 - Thin sensors, typical thickness 50 µm
 - Low to moderate gain (5-50) provided by p⁺ multiplication layer
 - Timing resolution down to ca. 20 ps \succ
 - Good radiation hardness up to 10¹⁵ n_{eg}/cm²

A more recent development: AC-coupled LGAD



H. F.-W. Sadrozinski et al, 4D tracking with ultra-fast silicon detectors, Reports on Progress in Physics 2018, 81, 026101 CMS Collaboration, A MIP Timing Detector for the CMS Phase-2 Upgrade, CERN-LHCC-2019-003, 2019 ATLAS Collaboration, A High-Granularity Timing Detector for the ATLAS Phase-II Upgrade, CERN-LHCC-2018-023, 2018



AC-coupled low gain avalanche diodes

- In AC-coupled LGADs, also referred to as Resistive Silicon Detectors (RSD), the multiplication layer and n⁺ contact are continuous, only the metal is patterned:
 - > The signal is read out from metal pads on top of a continuous layer of dielectric
 - The underlying resistive n⁺ implant is contacted only by a separate grounding contact
 - No junction termination extension: fill factor ~100
- The continuous n⁺ layer is resistive, i.e. extraction of charges is not direct
 - Mirroring of charge at the n⁺ layer on the metal pads: AC-coupling
 - Strong sharing of charge between metal pads
 - Extrapolation of position based on signal sharing finer position resolution for larger pitch, also allowing for more sparse readout channels



G. Giacomini et al., Fabrication and performance of AC-coupled LGADs, JINST 2019, 14, P09004

- A. Apresyan et al., Measurements of an AC-LGAD strip sensor with a 120 GeV proton beam, JINST 2020, 15, P09038
- S. M. Mazza, An LGAD-Based Full Active Target for the PIONEER Experiment, Instruments 2021, 5(4), 40



PIONEER Experiment

- New pion decay experiment approved at PSI, data taking to be started in 2028 - first beam time assigned in May 2022, next November 2023
- Design baseline for the Active TARget: 2x2 cm² area with 48 planes of 120 μm thick AC-LGAD strips, pitch ca. 200 μm
 - Large energy deposition by stopping particles: need sufficient charge sharing to provide good spatial resolution, but not enough to occupy large areas of the sensor from one hit





Cf. Adam's talk

PIONEER: Studies of Rare Pion Decays, https://arxiv.org/abs/2203.01981 (2022) S. M. Mazza, An LGAD-Based Full Active Target for the PIONEER Experiment, *Instruments* **2021**, *5*(4), 40



EPIC detector at the Electron-Ion Collider

- EIC Detector 1: recently issued recommendation, based on two protocollaborations
 - Emerged as ePIC Detector collaboration in summer 2022
- Design includes AC-LGADs for time-of-flight particle ID, t₀ determination and timing, and serving as additional layer in Tracking

Efforts organized in the TOF-PID working group, and eRD112/LGAD consortium
8.5 m



5.3 m



- EIC Detector 1: recently issued recommendation, based on two proto-collaborations
 - Emerged as ePIC Detector collaboration in summer 2022
- Design includes AC-LGADs for time-of-flight particle ID, t₀ determination and timing, and serving as additional layer in Tracking
 - Efforts organized in the TOF-PID working group, and eRD112/LGAD consortium
- Radiation hardness of timing detectors not very challenging more important:
 - Combination of precise temporal and spatial resolution: 25 ps and 30 μm / hit
 - Low material budget
- Current sensor design baseline:
 - Barrel: strips, 500 μm pitch and 1 cm length
 - Hadronic endcap (and Roman Pots): pads, 500 x 500 μm



- First design plans based on earlier generic AC-LGAD productions by FBK, BNL, HPK
 - Various electrode geometries, typically smaller sizes
 - Resistive n-layer and dielectric capacitance variation by HPK and FBK
- More targeted production(s) by BNL to evaluate strip pitch and width
 Cf. Artur's talk
- Beginning to fabricate 20 μm sensors in addition to the standard 50 μm
- Recent (2023) production by HPK aimed at EIC sensor specifications
- Focusing on 500 μm pitch baseline
- BNL productions focusing on gain layer engineering



HPK production splits:

- E and C type n-layer (E resistivity higher, C lower)
- Dielectric capacitance 240 and 600 pF/mm2
 - 20 and 50 μm bulk thickness for 600 pF/mm2
- Strips:
 - 2, 5, 10, 20, 25 mm length
 - 50, 100 µm width
- Pixels:
 - 150, 300, 450 µm pixel size

50 um Thick - E type - 240 pF/mm^2
50 um Thick - C type - 240 pF/mm^2
50 um Thick - E type - 600 pF/mm^2
50 um Thick - C type - 600 pF/mm^2
20 um Thick - E type - 600 pF/mm^2
20 um Thick - C type - 600 pF/mm^2

- Breakdown voltages ca. 210 V for 50 μm , 120 V for 20 μm thicknesses; gain layer depletion at ca. 50 V



- Radiation hardness: has not been extensively studied specifically for AC-LGADs
- Subset of HPK (and BNL) sensors were sent to Los Alamos National Lab for irradiation with 800 MeV protons in August
 - Focus on E type
 - Focus on 600 pF/mm² dielectric capacitance
 - Focus on 1cm strip length, 100 μm strip width, 150 μm pad size
- Total fluences between 1e13 and 2e14 p/cm² higher than envisioned at the EIC over the full time of life,
- Including attempts at graded irradiation of strip sensors to study the effects of non-uniform degradation of the gain layer and n-layer within a long sensor



Characterization of AC-LGADs: signal sharing

- Impact of sensor geometry, coupling dielectric, and n+ layer resistivity on signal sharing: essential question for any AC-LGAD detector
- Charge sharing to far-away strips has been the main problem in long strip sensors in the past
- Significant improvement in recent sensors





HPK strip sensors: laser studies

- Set of sensors at UCSC which have not been sent to LANL for irradiation: measured by infrared laser scanning TCT
 - Focus on 50 μm strip width
- Averaged waveform at each x-y point
- Time-of-arrival information and jitter based on laser reference
- Monitoring of sensor response uniformity, gain 'hotspots'









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• Selection for comparison:

HPK ID	Geometry	wafer	position	size	HPK n+ layer doping	Nominal dielectric C (pF/mm2)	thickness	lenght (mm)	pitch (um)	width (um)
HPK29	Strip	W09			E	600	20	20	500	50
HPK35	Strip	W09			E	600	20	20	500	100
НРК8	Strip	W04			с	240	50	5	500	100
HPK4	Strip	W08			С	600	50	5	500	50
HPK4	Strip	W08		1	C	600	50	5	500	50
НРК3	Strip	W05		(E	600	50	5	500	50
HPK8	Strip	W04			С	240	50	5	500	100
HPK1	Strip	W02			E	240	50	5	500	50
HPK27	Strip	W05			E	600	50	20	500	50
HPK21	Strip	W05			E	600	50	10	500	100
HPK3	Strip	W05			E	600	50	5	500	50
HPK27	Strip	W05			E	600	50	20	500	50
HPK3	Strip	W05			E	600	50	5	500	50
HPK27	Strip	W05			E	600	50	20	500	50
HPK29	Strip	W09			E	600	20	20	500	50



- Larger signal sharing has been observed in longer strips was not considered a factor originally
- Promising efforts to replicate this in TCAD simulation and correlate it to strip capacitances and resistances
- For E600 type sensors, strip length is indeed confirmed to increase charge sharing with the neighboring strip, however likely not to a detrimental degree (< 15 % at the next strip) even for 2 cm long samples
- Encouraging to consider longer strips than the baseline design: would reduce number of readout channels





- 50 μm has been a standard active thickness for LGAD sensors
- To lower the contribution of Landau fluctuations in charge deposition and signal induction, thinning of the sensor bulk (20 μm ~established, in the future even further) is desirable
 - Cons: smaller intrinsic signal; lower breakdown voltage = carrier drift velocity does not saturate unless gain layer is modified
- In 2 cm sensors, at comparable gain, the bulk thickness does not have a significant impact on the signal sharing
- Signal amplitude profile between main strips differs: quantification of expected spatial and timing resolution to be investigated





- Expected to be one of the most important parameters in AC-LGADs
- Not fully conclusive results in earlier sensors
- Effect very clearly visible in the HPK production: show-stopper for strip sensors, however increased sharing may be needed in small pad sensors in order to not lose efficiency at the relatively large 500 µm pitch
- Significant long-distance sharing in the C type sensor, increasing towards the edge n-layer contact: how would this affect larger – in this case wider – sensors even if strip length is restricted?





HPK strip sensors: laser studies

In terms of signal sharing / signal amplitude:

- Signal sharing is strongly impacted by the n-layer resistivity – almost 20 % more for lower resistivity, as well as different longrange behavior
- Strip length increases signal sharing, but signal from primary channel decreases down to ~10% at the next neighbor
- Roles of sensor bulk thickness, strip width, dielectric capacitance are less significant



Sensor type



 Ongoing effort to link signal sharing to capacitances – stay tuned!



More details:

https://indico.cern.ch/event/829863/contributions/5061072/attachments/2564834/4422979/JOtt_Pixel2022.pdf https://indico.bnl.gov/event/20281/contributions/79620/attachments/49124/83705/JOtt_eRD112_CV_update_Aug23.pdf



- Quantification of reduced signal amplitude and timing delay in long strips
- Charge sharing along (parallel to) the strip
- Time-of-arrival and timing resolution parallel to a strip
- Systematic studies on pad sensors, intrinsic position reconstruction based on charge sharing
- Angular dependence of abovementioned properties

Identify optimal parameters for strip and pad sensors for specific applications



- Large-scale sensor productions
 - Uniformity of gain implantation
 - 'Large' sensors (e.g. 2x4 cm strips)
 - Fabrication, yield
 - Vendor qualification
- Readout electronics
 - Electronics for precision timing are being developed
 - Sensor size and input capacitances need to be specified
- Detector system integration
 - Assembly into modules: glueing, mechanics
 - Profit from previous experiences in strip detectors as well as ATLAS/CMS endcap timing layers, but timelines of developments overlap



- Standalone timing layers or integration into 4D (5D) Trackers?
 - Integration of gain layer in CMOS sensors...
- Occupancy:
 - Challenging for resistive layers
 - AC-coupling may not be ideal or necessary: DC-coupled resistive detectors? (in production at FBK)
- Radiation hardness: similar problems related to gain layer radiation hardness as other LGADs, potentially additional features
 - Partially compensated boron doping
- Segmentation
 - AC-LGADs can achieve better position resolution through charge sharing – may come at expense of timing performance
 - Deep-junction LGAD or deep gain layer